

30W Active Clamp Flyback

Application note AN1110 describes how to utilize Silanna's primary-side controller SZ1110 to design 30w high power density active clamp flyback converters for USB-PD applications.

Introduction

The SZ1110 is an Active clamp Flyback (ACF) PWM Controller that integrates an adaptive digital PWM controller and the following Ultra High-Voltage (UHV) components: active clamp FET, active clamp driver and a start-up regulator.

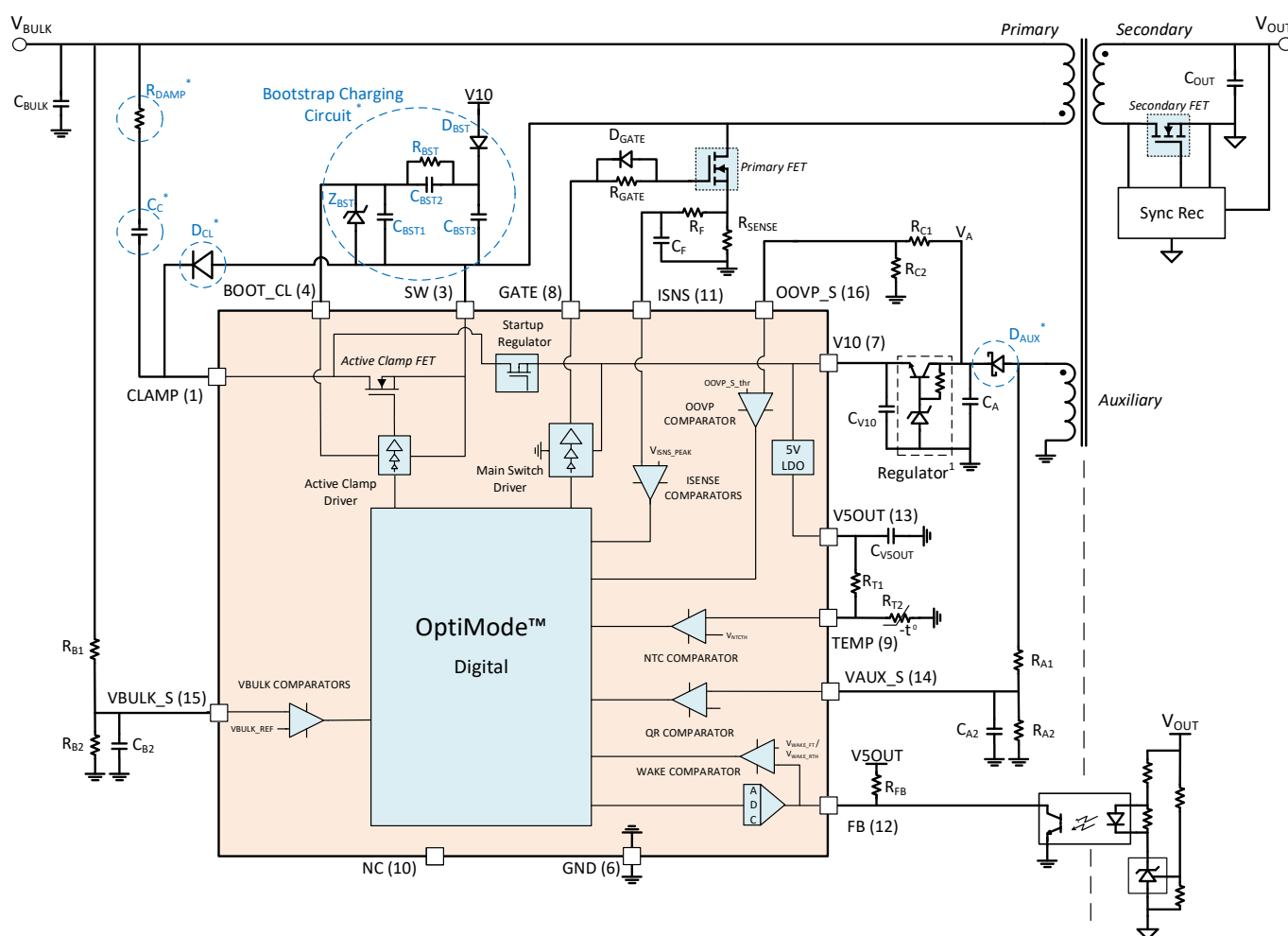


Figure 1: Typical Application Circuit of an Active clamp Flyback Converter using SZ1110

The device provides ease-of-design of a simple flyback controller with all the benefits of an ACF design, including recycling of the flyback transformer leakage energy and clamping of the primary FET drain voltage. Employing Silanna's OptiMode™ digital control architecture, the SZ1110 adjusts the device's mode of operation on a cycle-by-cycle basis to maintain high efficiency, low EMI, and fast dynamic load regulation.

Unlike conventional ACF designs, tight tolerances of the clamp capacitor and leakage inductance values are not required for proper operation of the circuit. Moreover, a small 3.3nF clamp capacitor is sufficient to realize the benefits of ACF operation. The SZ1110 is well suited for high efficiency and high-power density AC/DC power adapters. The device is designed for up to 30 w output power, including USB PD and Quick Charge applications.

Parameter	Min.	Typ.	Max	Unit
Input Parameters				
Line Voltage	90	-	264	Vrms
Line Frequency	47	60	63	Hz
Output Parameters				
Max output voltage		20		V
Min output voltage		5		V
Max output Power		30		W
Max output current		3		A
Over Current Limit		110		%

Table 1: Converter specification data

Design Procedure

Transformer design

This section provides detailed step by step procedure for designing a flyback converter. A 30W USB-PD (5-20V) charger has been selected as a design example.

Step 1: Estimate the input power

Assuming 20% over-current limit (OCL) allowance the maximum output power will be

$$P_{out}^{max} = P_{out} \cdot OCL$$

and the maximum input power as seen at the bulk capacitor is,

$$P_{in}^{max} = \frac{P_{out}^{max}}{\eta^{bulk}}$$

where η^{bulk} is the minimum efficiency of the converter from the bulk capacitor to the output capacitor, typically 94%.

Design Example

The maximum output power is obtained using equation 1:

$$P_{out}^{max} = 30 \cdot 1.1 = 33W$$

The maximum input power is obtained using equation 2:

$$P_{in}^{max} = \frac{33W}{0.94} = 35W$$

Step 2: Determine the input bulk capacitance value

For universal AC line applications, bulk capacitance values equal to ~1.5uF per watt of input power are recommended in order to maximize efficiency and provide sufficient stored energy for continuous operation during IEC-61000-4-11 type voltage sag events. For applications where low AC line operation requirements are relaxed (either in terms of maximum output power, efficiency or voltage sag ride-through), the bulk capacitance values can be minimized.

For universal AC line applications, the recommended bulk capacitance value is

$$C_{bulk} = 1.5 \cdot P_{in}^{max}$$

If the above recommendation is not followed it is imperative that the capacitance value be chosen such that the minimum bulk voltage, v_{bulk_min} , is greater than SZ1110 brown-out threshold (recommendation 70V).

$$C_{bulk} > \frac{P_{in}^{max} \cdot (1 - D_{ch})}{f_{ac}} \cdot \frac{1}{2v_{ac_min}^2 - v_{bulk_min}^2}$$

where, v_{bulk_min} is the minimum input line voltage, P_{in}^{max} is the maximum input power, D_{ch} is the bulk capacitor charging duty ratio defined as shown in Figure 2: Input bulk capacitor voltage waveform

, C_{bulk} is the bulk capacitance, f_{ac} is the minimum AC line frequency.

The charging duty ratio, D_{ch} can be calculated as

$$D_{ch} = \frac{\frac{1}{4f_{ac}} - \frac{\sin^{-1}\left(\frac{v_{bulk_min}}{\sqrt{2} v_{ac_min}}\right)}{2\pi f_{ac}}}{\frac{1}{2f_{ac}}}$$

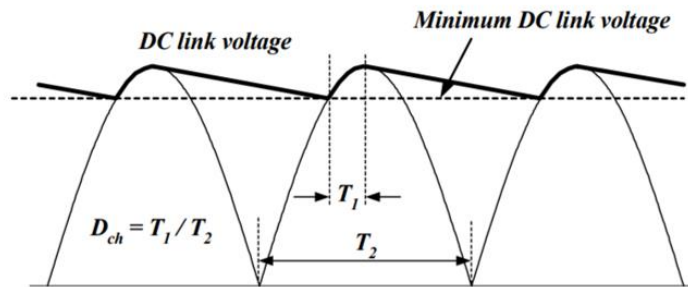


Figure 2: Input bulk capacitor voltage waveform

Design Example - C_{bulk} calculation

Assuming converter specifications outlined in Table 1, D_{ch} & C_{Bulk} can be calculated using the above equations:

$$D_{ch} = \frac{\frac{1}{4f_{ac}} - \frac{\sin^{-1}\left(\frac{v_{bulk_min}}{\sqrt{2} v_{ac_min}}\right)}{2\pi f_{ac}}}{\frac{1}{2f_{ac}}} = \frac{\frac{1}{4 \cdot 47} - \frac{\sin^{-1}\left(\frac{70}{\sqrt{2} \cdot 90}\right)}{2\pi \cdot 47}}{\frac{1}{2 \cdot 47}} = 0.315$$

$$C_{bulk} > \frac{P_{in}^{max} \cdot (1 - D_{ch})}{f_{ac}} \cdot \frac{1}{2v_{ac_min}^2 - v_{bulk_min}^2}$$

$$C_{bulk} > \frac{35 \cdot 0.685}{47} \cdot \frac{1}{2 \cdot 90^2 - 70^2} = 45\mu F \approx 47\mu F \text{ (standard value)}$$

Step 3: Calculating primary-to-secondary turns ratio and primary magnetizing inductance

When the primary FET is off and the secondary side switch is conducting, the secondary side winding voltage is reflected on the primary winding. During this period, the primary FET drain and SZ1110 SW pin, V_{SW} , is exposed to a voltage approximately equal to reflected secondary winding voltage (VVOR) plus the maximum bulk voltage (V_{bulk}). To ensure reliable operation of SZ1110 it is recommended that the maximum reflected secondary winding voltage, specifically the primary to secondary side transformer turns ratio, be selected in such a way that the primary FET peak drain and SW pin voltages are kept below 90% of the SZ1110 SW node maximum voltage rating, 620V.

The primary magnetizing inductance (L_M) can be calculated using,

$$L_M < \frac{(D_{max} * V_{bulk_min})^2}{2 * P_{IN_MAX} * PCL_{\Delta} * f_{sw_min}}$$

Where f_{sw_min} is the minimum converter switching frequency, PCL_{Δ} is the peak-current limit variation (1.14) and D_{max} is the maximum primary side MOSFET duty cycle.

Design Example

The maximum allowable voltage at the drain of the FET/SW pin is, (NCE 65T900K is used as an illustration for the App note)

$$V_{SW} = V_{SW}^{max} \cdot 0.9 = 620V \cdot 0.9 = 558V$$

The maximum allowable reflected voltage, V_{VOR}^{max} , is given by the maximum allowable SW pin voltage and maximum bulk voltage ($1.1 \cdot V_{AC}^{max} \cdot \sqrt{2}$),

$$V_{VOR}^{max} = V_{SW} - V_{bulk}^{max} = 558V - (1.1 \cdot 265V_{RMS} \cdot 1.414) = 148V$$

The primary to secondary turns ratio can be calculated using the maximum allowable reflected voltage and maximum output voltage.

$$n = V_{VOR}^{max} / 1.05 \cdot V_{out}^{max}$$

$$n = 148V / 21V = 7$$

(Note: this is an approximation that does not take into account the clamp capacitor voltage ripple. The maximum primary side MOSFET drain-source voltage should be verified experimentally, or the design tool utilized to derive more accurate estimates)

During max duty-cycle operation it can be assumed that the flyback converter will be operating near boundary mode conduction and that the max duty cycle of the converter, D_{max} , is given by

$$D_{max} \approx V_{VOR} / (V_{bulk}^{min} + V_{VOR})$$

$$D_{max} \approx 140V / (70V + 140V) = 0.67$$

The minimum switching frequency is selected to be in the 60-80kHz range (lower frequency for optimized high-line efficiency and higher frequency for optimized low-line efficiency).

$$f_{sw_min} = 70kHz$$

Substituting the values in the equation:

$$L_M < \frac{(0.67 \cdot 70)^2}{2 \cdot 35 \cdot 1.14 \cdot 70k} = 396\mu H$$

The selected value for L_m is 390uH.

Step 4: Core Selection and Primary Turns Calculation

The minimum number of primary turns (N_{P_min}) can be calculated using the formula

$$N_{P_min} = \frac{L_M \cdot I_{max}}{B_{max} \cdot A_e} \cdot 10^6$$

where I_{max} is the maximum transformer primary current, A_e is the minimum equivalent magnetic core cross-sectional area in mm^2 and B_{max} is the saturation flux density in tesla (typically 0.3-0.34T).

Design Example (3C95 RM7)**Primary/Secondary Turns Calculation**

$$I_{max} = \frac{V_{bulk_min} \cdot D_{max}}{L_m \cdot f_{sw_min}} I_{max} = \frac{70V \cdot 0.67}{390\mu H \cdot 70kHz} = 1.72A$$

Note : With the 47uF Bulk cap , the new V_{bulk_min} is higher than 70V is used in the calculation to account for any worst-case condition.

$$N_{P_min} = \frac{L_m \cdot I_{max}}{B_{max} \cdot A_e} \times 10^6$$

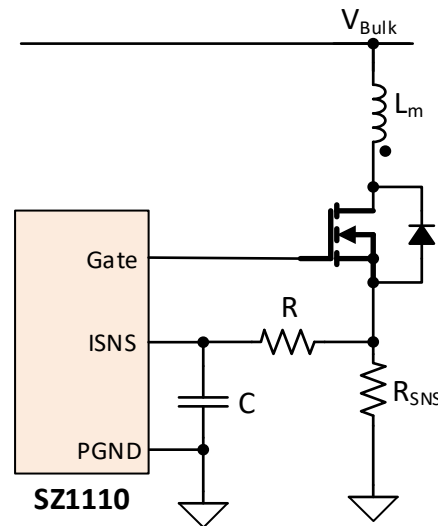
$$N_{P_min} = \frac{390\mu H \cdot 1.72A}{0.33T \cdot 39 mm^2} \times 10^6$$

$$N_{P_min} = 49 T$$

$$N_s \geq \frac{N_{P_min}}{n}$$

$$N_s \geq \frac{49}{7} = 7T$$

$$N_s = 7 T$$

Step 5: R_{SNS} calculation and RC filter selection guideFigure 3: R_{SNS} and RC filter circuit

SZ1110 implements two different ISNS thresholds. The skip pulse current threshold (V_{ISNS_SKIP}) is enabled during the light load operating conditions to improve efficiency. The peak current limit threshold (V_{ISNS_PEAK}) protection is to ensure the transformer does not saturate beyond I_{max} value and also to implement over power protection (OPP).

The formula to calculate R_{SNS} is given by

$$R_{SNS} = \frac{V_{ISNS_PEAK}}{I_{MAX}}$$

where V_{ISNS_PEAK} is the maximum peak-current limit, as defined in datasheet, equal to 285mV.

Design Example

$$R_{SNS} = \frac{285mV}{1.72A} = 165m\Omega$$

High frequency noise mitigation

To mitigate the effects of leading-edge current sensing noise, SZ1110 implements digital blanking, t_{ISNS_BLNK} (minimum value 221ns), of the current sensing comparator outputs. The main motivation is to ensure that the skip-pulse current limit (V_{ISNS_SKIP}) is enforced during light load mode of operation and that high-frequency noise does not cause reduced primary MOSFET on-time, which can negatively affect efficiency and BOOT_CL charging (AC FET ability to turn-on).

One example where additional RC filter between the R_{SNS} resistor and ISNS pin is necessary is shown in Figure 4.

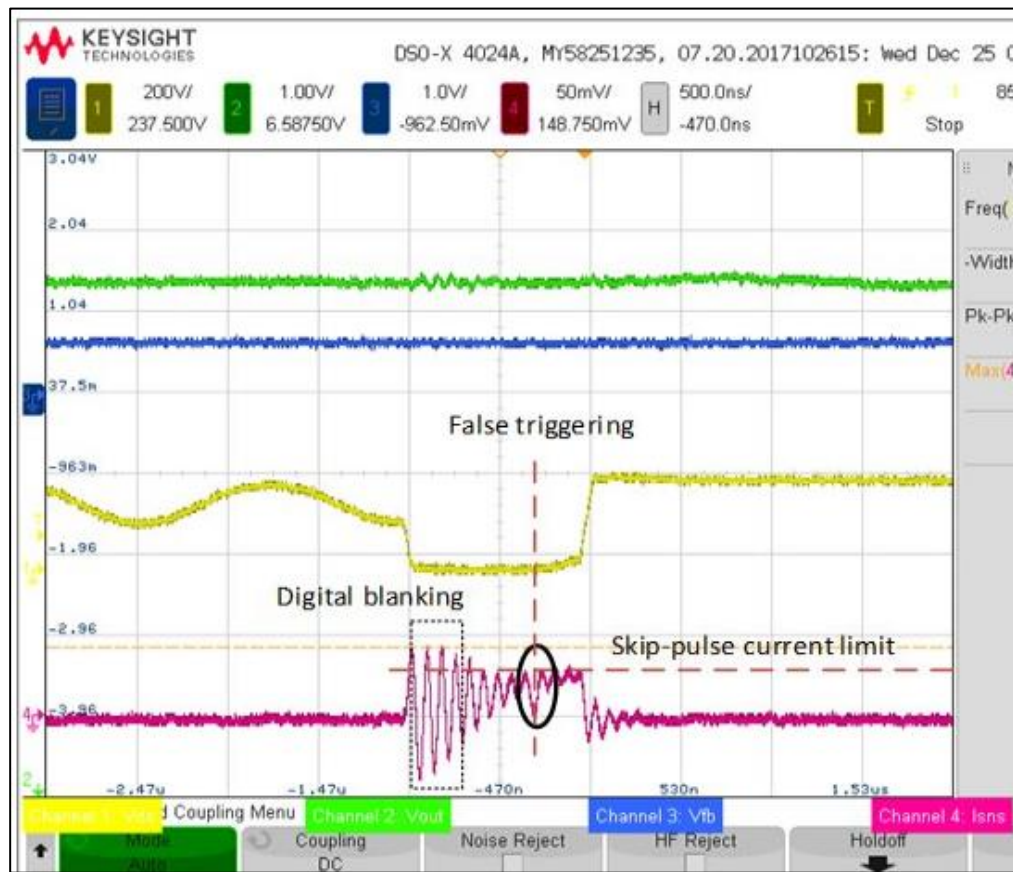


Figure 4: False triggering of skip-pulse current limit of due to high frequency noise

It should be noted that when a R_{SNS} RC filter is utilized it will result in higher skip-pulse and peak-current limits due to the added delay in detection. As a result, the peak-current limit value will increase by an amount equal to

$$i_{PCL}^{\Delta} = (1+\alpha) \cdot \frac{BULK}{L_M} \cdot R \cdot C,$$

where α is given by

VBULK_S (DC)	α
<0.95V	0.75
$\geq 0.95V, < 1.7V$	0.50
$\geq 1.7V, < OVLO$	0.375

Table 2: VBULK_S and corresponding α value

To maintain flat over-power protection, it is recommended that the RC filter be minimized to value less than 240ns ($R = 10-24R$ and $C = 10nF$).

The skip-pulse current limit value will increase by an amount equal to

$$i_{SPL}^{\Delta} = \frac{BULK}{L_M} \cdot R \cdot C.$$

Minimization of output voltage ripple during light-load operation via reduction of SPL threshold

Certain applications may require <100mVpk-pk output voltage ripple during low output voltage and light-load operation. For these applications, this can be achieved by a reduction of the SPL threshold using the circuit shown in Figure 5.

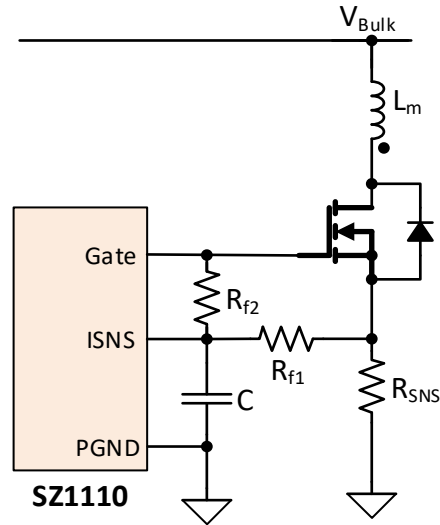


Figure 5: R_{SNS} and RC filter circuit

The SPL current reduction, as a relative ratio of SPL threshold, is given by equation

$$i_{SPL}^{\Delta ratio} = \frac{1}{1 + \frac{R_{f2}}{R_{f1}}}$$

Typical range of R_{f2} values that will ensure 70 to 80mV output voltage ripple during 5V output voltage operation are 16 to 20k Ω .

Step 6: Gate resistor sizing

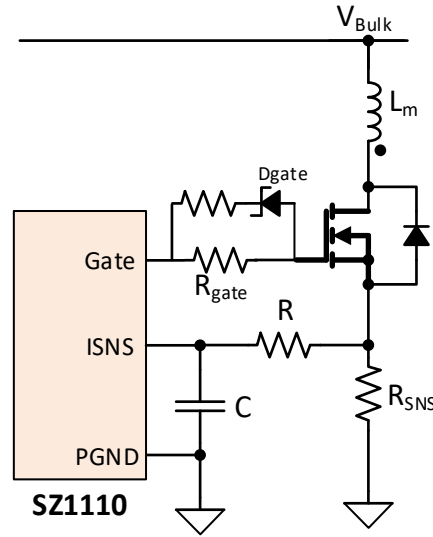


Figure 6: External gate resistor in series with the Main FET

If an external series resistor is added in series with the gate of the primary FET to slow down the turn-on, reducing the falling dV/dt of the switching node (drain of the primary FET), care must be taken in order to ensure that the effective on-time of the primary FET is sufficiently long enough to charge the BOOT_CL capacitor during the first start-up pulse. The maximum value of R_{gate} that can be used is given by the following equation.

$$R_{GATE}^{max} = \frac{120ns}{\frac{Q_{gd}}{4 \cdot (V_{OFF_V10}^{min} - V_{plateau})} + \frac{2 \cdot C_{iss} \cdot V_{gs}^{th_MAX}}{V_{OFF_V10}^{min} + V_{gs}^{th_MAX}}} - R_{GATE_PUP}^{max} - R_{INT_GATE_FET}$$

where Q_{gd} is the primary MOSFET gate-to-drain charge ($V_{DS}=374V$), C_{iss} is the primary MOSFET input capacitance ($V_{DS}=374V$), $V_{OFF_V10}^{min}$ is the minimum startup regulator turn-off threshold, $V_{plateau}$ is the expected plateau voltage of the primary MOSFET ($V_{DS}=374V$, $I_{DS}=0A$), $V_{gs}^{th_MAX}$ is the primary MOSFET maximum gate-source threshold, $R_{INT_GATE_FET}$ is the primary MOSFET internal gate resistance and $R_{GATE_PUP}^{max}$ is the maximum internal gate-driver pull-up resistor.

A low forward voltage drop diode ($<0.4V$ @ $1A$), D_{GATE} , in parallel with R_{GATE} should be added to avoid deterioration of the primary FET turn-on time. In such a way, turn-off switching losses can be minimized. Furthermore, the non-repetitive peak forward current capability of D_{GATE} should be greater than

$$I_{RGATE}^{repetitive} \geq \frac{V_{V10}^{max}}{R_{GATE_PDN}^{min} + R_{INT_GATE_FET}}$$

Design Example

The MOSFET chosen is NCE Power's NCE65T900. The maximum R_{GATE} can then be calculated as:

$$R_{GATE}^{max} = \frac{120ns}{\frac{Q_{gd}}{4 \cdot (V_{OFF_V10}^{min} - V_{plateau})} + \frac{2 \cdot C_{iss} \cdot V_{gs}^{th_MAX}}{V_{OFF_V10}^{min} + V_{gs}^{th_MAX}}} - R_{GATE_PUP}^{max} - R_{INT_GATE_FET}$$

$$= \frac{120ns}{\frac{5.3nC}{4 \cdot (9.35V - 5V)} + \frac{2 \cdot 0.37nF \cdot 4V}{9.35V + 4}} - 86\Omega = 142\Omega$$

The non-repetitive peak forward current is calculated as:

$$I_{RGATE}^{repetitive} \geq \frac{10.5V}{2.9\Omega} = 3.6A$$

PMEG2005AEA,115 was chosen for D_{GATE} as it meets all the requirements within a compact SOD323 package.

Step 7: Bias winding turns and bias capacitance calculation

The design of the two-level bias winding starts with establishing the number of bias turns required for sufficient bias capacitor and V_{IO} voltage during no-load.

During no load operation the converter operates in burst mode, issuing at least 4 cycles per burst. While in burst mode, the V_{IO} pin voltage must be maintained above V_{ON_VIO} in order to guarantee that the internal UHV startup regulator remains off.

In order to calculate the required bias capacitor voltage and bias turns ratio, the burst repetition rate and the charge delivered per burst are required. Total charge delivered by 4 pulses is given by

$$Q_{burst_4pulses} = 2 \cdot (I_{burst}^{peak})^2 \cdot \frac{L_m}{V_{out}}$$

Where L_m is the transformer magnetizing inductance, V_{out} is the output voltage, and I_{burst}^{peak} is the peak primary FET current during burst mode.

$$I_{burst}^{peak} = \frac{50mV}{R_{SNS}}$$

The time between bursts can now be calculated.

$$t_{burst} = \frac{Q_{burst}^4}{I_{out}}$$

Where I_{out} is no load secondary current.

Using t_{burst} the top winding $C_{auxiliary}$ capacitance, can now be calculated.

$$C_{aux} = \frac{I_{ic} \cdot t_{burst}}{\Delta V_{aux}}$$

The auxiliary winding must provide V_{ON_V10} for IC operation and also compensate for regulator drop, diode voltage and $V_{auxiliary}$ ripple.

$$V_{aux} = 8.55V + \text{regulator drop} + \text{diode voltage drop} + V_{auxiliary} \text{ ripple}$$

$$N_{aux} \geq \left(\frac{N_{sec}}{V_{out_min}} \right) \cdot V_{bias}$$

Design Example – Top Bias Winding turns and capacitance

Primary/Secondary Turns Calculation

$$I_{burst_peak} = \frac{50mV}{0.165\Omega} = 0.3A$$

Four pulses of 0.3A will deliver a total charge equal to:

$$Q_{burst_4pulses} = 2 \cdot (0.3A)^2 \cdot \left(\frac{390\mu H}{5V} \right) = 1.4 \times 10^{-5}C$$

The time between bursts can now be calculated, assuming no load secondary current of 1.4mA (in actual designs it will be dependent on PD controller that is used and feedback network).

$$t_{burst} = \frac{1.4 \times 10^{-5}C}{1.4mA} = 10ms$$

Using t_{burst} , $V_{I/O}$ input supply no-load current 2.9mA (datasheet) and assuming 2V as $V_{auxiliary}$ ripple the $C_{auxiliary}$ capacitor can now be calculated

$$C_{aux} = \frac{2.9mA \cdot 10ms}{2V} = 14.5\mu F \rightarrow 22\mu F \text{ (standard value)}$$

Calculating N_{bias} must provide 8.55V for IC operation, ~1.2V for regulator drop, 0.4V for diode voltage, and 2V to compensate for $V_{auxiliary}$ ripple. Therefore the winding must produce:

$$V_{aux} = 8.55V + 1.2V + 0.4V + 2V = 12.15$$

$$N_{aux} \geq \left(\frac{N_{sec}}{V_{out_min}} \right) \cdot V_{aux} \geq \frac{7T}{5V} \cdot 12.15V = 17T$$

Use 17T for N_{aux} .

Design Example – Bottom Bias Winding turns and capacitance

To calculate the bottom bias winding tap position, the output voltage at which the tap becomes active must be selected. This selection can be based on desired efficiency optimization and/or dual auxiliary component voltage ratings, in this example the maximum output voltage is selected.

To provide the minimum V_{bias} voltage at 15V output voltage, the bias winding tap must provide 8.55V for IC operation, ~1.2V for regulator drop, 0.4V for diode voltage and 2V to compensate for the $V_{auxiliary}$ ripple

$$V_{bias} = 8.55V + 1.2V + 0.4V + 2V = 12.15V$$

$$N_{tap} \geq \left(\frac{N_{sec}}{V_{out}} \right) \cdot V_{bias_{tap}} = \frac{7T}{15V} \cdot 12.15V \geq 5.7T \text{ (6T)}$$

The bottom bias winding capacitance value is calculated such that it's discharge rate is slower than the bus capacitance discharge rate in case of output over voltage fault. This is required in order to ensure that when SZ1110 hiccups (restarts) there are no circulating currents from the output bus to the bias winding capacitors, which can cause large voltage spikes on the secondary side MOSFET.

$$C_{aux}^{bottom} \geq C_{bus} \cdot \frac{I_{V10}^{fault}}{I_{VOVP}^{OOVP}} = 660\mu F \cdot \frac{0.7mA}{7mA} = 66\mu F$$

It should be noted that most PD ICs support active discharging of the output bus node in case of output over voltage events. If such a feature exists it is highly desirable that it is enabled since it will significantly reduce the required C_{aux}^{bottom} . An example is shown below where a 20mA discharge current is enabled during output over voltage event.

$$C_{aux}^{bottom} \geq C_{bus} \cdot \frac{I_{V10}^{fault}}{I_{VOVP}^{OOVP}} = 660\mu F \cdot \frac{0.7mA}{20mA} \approx 22\mu F$$

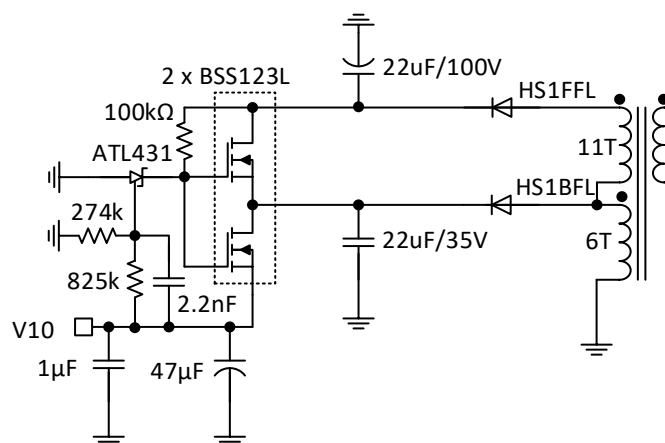


Figure 7: Dual-winding auxiliary regulator circuit for high performance USB PD applications

Step 8: Core gap

With the determined turns of the primary side, the gap length of the core is obtained as

$$l_g \approx \mu_0 \frac{N_{pri} \cdot I_{max}}{B_{max}} \cdot \text{mm.}$$

Design Example: Gap Calculation

As only a minimal amount of energy is stored in the core itself, this factor may be ignored to simplify calculation.

$$l_g = 4\pi \cdot 10^{-7} \cdot \frac{49T \cdot 1.72A}{0.33T} = 0.32mm$$

Step 9: Determine the wire diameter

The recommended bobbin for the design example is B65820W1008D001 and the specifications are shown below:

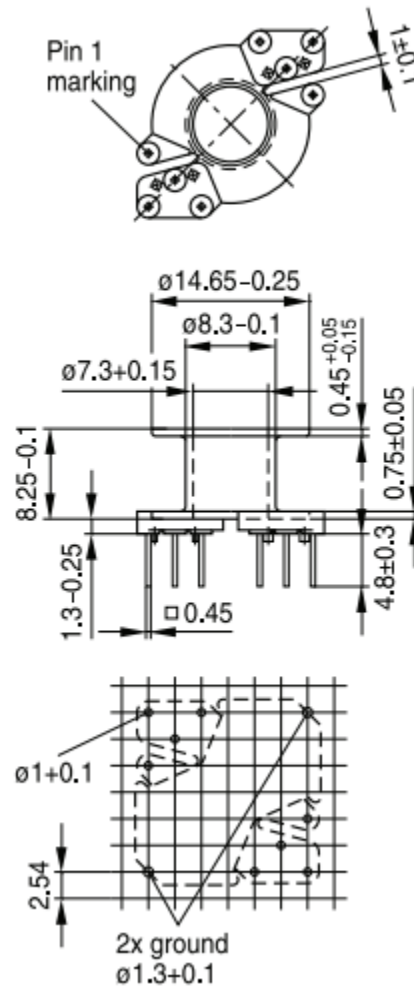


Figure 8: B65820W1008D001 bobbin specifications

The objective is to determine the appropriate wire diameter & number of strands so that copper losses (DC & AC resistance) are minimized. The first step is to determine the primary winding diameter. The primary winding diameter is calculated based on the skin depth to minimize the AC loss.

For the primary magnetizing current, which is a triangular shaped waveform, the major harmonics are the 1st and the 3rd.

Skin depth for the 3rd harmonic can be calculated as, $\delta = \sqrt{\frac{\rho}{\pi \cdot \mu_0 \cdot \mu_r \cdot f}}$

where,

ρ is the resistivity of the wire material (copper)

μ_o = permeability of free space

μ_r is the relative magnetic permeability of the wire material,

f is the frequency of interest.

$$\delta = \sqrt{\frac{2.3 \cdot 10^{-8}}{\pi \cdot 4\pi \cdot 10^{-7} \cdot 300k}} = 0.139mm$$

Assuming a fill factor of 90%, the maximum primary winding radius can be calculated as below:

$$\text{Fill factor} = \frac{(2 \cdot \text{primary winding radius}) \cdot \frac{N_p}{\text{number of primary layers}}}{\text{Winding_area_length}}$$

$$0.90 = \frac{(2 \cdot \text{primary winding radius}) \cdot \frac{49}{2}}{6.85}$$

Primary winding radius = 0.126 mm

Since the calculated skin depth δ is 0.139mm, single strand of wire is sufficient. The closest to that is AWG30 (0.127 mm).

Once the wire size is determined, it is a good practice to calculate the current capacity (circular mils per amp or CMA).

$$\text{Circular Mil per Amp, CMA} = \frac{\text{CM of the winding} \cdot \text{No of parallel winding}}{I_{rms}}$$

For a nominal operating condition, $V_{ac}=90V_{rms}$, $V_{out}=20V$, $I_{out}=1.5A$ and $C_{bulk}=47\mu F$, $L_m=390\mu H$, $N_p=49T$, $N_s=7T$. The calculated primary I_{rms} value is ~0.52A.

$$\text{Circular Mil per Amp, CMA} = \frac{100.5 \cdot 1}{0.52} = 193.$$

The calculated CMA value is on the lower end of the nominal (200~500) range. This is the design trade-off to use RM7 Core and interleave winding structure. If the CMA value calculated is not acceptable then iteration is required to increase the CM of the winding which in turn may result in increasing the number of layers or choosing the next larger core size.

Secondary Winding

The secondary winding is usually a triple insulated wire i.e. it has three distinct layers of insulation, such that the insulation safety requirements between primary and secondary side is met. Like the primary, secondary current waveform is also triangular. Hence considering major harmonics 1st and 3rd, the calculated skin depth is 0.139mm.

$$\text{Secondary winding wire diameter} = \left(\frac{\text{Winding area length} * FF}{N_s} \right) = \frac{6.85 * 0.9}{7} = 0.98\text{mm} (0.0386\text{in})$$

Since the calculated skin depth δ is 0.139mm, the constraint is that the strand OD has to be AWG30 or higher AWG. From the table below, TXXL07/32TXXX-2 (MWXX) can be selected since its nominal OD is close to the theoretical calculations and meets the constraints.

PART NUMBER	EQUIV. AWG	CORE O.D. (in)	CIR. MILS	NO. STRANDS	AWG OF STRANDS	NOMINAL O.D.(in)
TXXL180/38TXXX-2(MWXX)	13.5	0.0694	2880	180	38	0.0814
TXXL180/38TXXX-3(MWXX)	13.5	0.0694	2880	180	38	0.0874
TXXL15/30TXXX-1.5(MWXX)	16.5	0.0485	1500	15	30	0.0575
TXXL15/30TXXX-2(MWXX)	16.5	0.0485	1500	15	30	0.0605
TXXL15/30TXXX-3(MWXX)	16.5	0.0485	1500	15	30	0.0665
TXXL360/44TXXX-2(MWXX)	15	0.0557	1440	360	44	0.0677
TXXL360/44TXXX-3(MWXX)	15	0.0557	1440	360	44	0.0737
TXXL19/36TXXX-2(MWXX)	21.5	0.0281	475	19	36	0.0401
TXXL19/36TXXX-3(MWXX)	21.5	0.0281	475	19	36	0.0461
TXXL35/38TXXX-2(MWXX)	21	0.0306	560	35	38	0.0426
TXXL35/38TXXX-3(MWXX)	21	0.0306	560	35	38	0.0486
TXXL07/30TXXX-1.5(MWXX)	20	0.0331	700	7	30	0.0421
TXXL07/30TXXX-2(MWXX)	20	0.0331	700	7	30	0.0451
TXXL230/44TXXX-2(MWXX)	17	0.0445	920	230	44	0.0565
TXXL230/44TXXX-3(MWXX)	17	0.0445	920	230	44	0.0625
TXXL40/40TXXX-1.5(MWXX)	22	0.0254	385	40	40	0.0344
TXXL40/40TXXX-2(MWXX)	22	0.0254	385	40	40	0.0374
TXXL07/32TXXX-1.5(MWXX)	21.5	0.0267	448	7	32	0.0357
TXXL07/32TXXX-2(MWXX)	21.5	0.0267	448	7	32	0.0387
TXXL19/40TXXX-1.5(MWXX)	25.5	0.0175	183	19	40	0.0265
TXXL19/40TXXX-2(MWXX)	25.5	0.0175	183	19	40	0.0295
TXXL05/32TXXX-1.5(MWXX)	23	0.0226	320	5	32	0.0316
TXXL05/32TXXX-2(MWXX)	23	0.0226	320	5	32	0.0346
TXXL16/44TXXX-1.5(MWXX)	30	0.0101	64	16	44	0.0191

Table 4: Wire Part Number and corresponding AWG & O.D value

Corresponding CMA value of the secondary winding can be calculated as:

$$\text{Circular Mil per Amp, CMA} = \frac{\text{CM of the winding} * \text{No of parallel winding}}{I_{rms}}$$

From the Table 4, the equivalent CMA value for the TXXL07/32TXXX-2 (MWXX) wire is 920. For the same nominal operating condition (as used in the primary winding CMA), the secondary Irms current was calculated as ~ 2.76A.

$$\text{Circular Mil per Amp, CMA} = \frac{448}{2.76} = 162$$

Auxiliary winding

For the auxiliary winding the recommended wire gauge is AWG 32 (0.202mm diameter), the number of layers is 1 and parallel wires is 1.

Step 10: Determine the active clamp external components

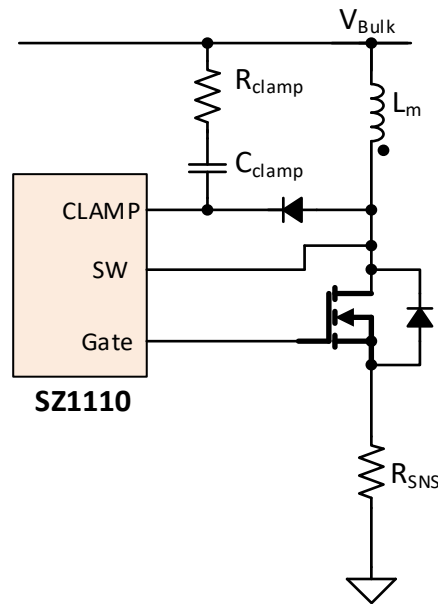


Figure 9: Clamp circuit consisting of active clamp capacitor, resistor and parallel diode.

The selection of the active clamp capacitor, C_{clamp} , is a two-step process. First, the initial estimation of C_{clamp} should be made based on the average transformer leakage inductance value, $L_{leakage}$, using the following equation.

$$C_{clamp} = \left(\frac{T_{RES}}{2\pi} \right)^2 \cdot \frac{1}{L_{leakage}}$$

Where, T_{RES} is the resonant period of C_{clamp} and $L_{leakage}$, which should be set to $1\mu s$. If $L_{leakage}$ is unknown, a reasonable estimate would be 1.5% of the primary side magnetizing inductance.

Second, check T_{RES} during full-power operation, at maximum output voltage, and adjust C_{clamp} to ensure 0.9- $1\mu s$ resonant period is achieved. Figure 10 identifies this resonant period from the drain voltage waveform of the primary FET after it turns off



Figure 10: Typical primary MOSFET drain voltage and active clamp current with the active clamp resonant period highlighted

The voltage rating of C_{clamp} needs to be calculated to withstand the DC component of reflected output voltage and the AC component of $\Delta V_{C_{clamp}}$:

$$V_{MIN_CC} = V_{OUT_MAX} \cdot \frac{N_{PRI}}{N_{SEC}} + \Delta V_{CC}$$

where the AC component ΔV_{CC} , is given by:

$$\begin{aligned} \Delta V_{CC} &\approx \frac{\pi}{4} \cdot I_{MAX} \cdot \sqrt{\frac{L_{LK}}{C_C}} \\ &= \frac{\pi}{4} \cdot \frac{V_{ISNS_PEAK}}{R_{SENSE}} \cdot \sqrt{\frac{L_{LK}}{C_C}} \end{aligned}$$

Design example

For the primary magnetizing inductance of 390uH, considering leakage inductance to be ~1.5% and setting the resonant period as 1us.

Leakage inductance = 1.5% $L_M = 5.85\mu\text{H}$

Capacitor clamp,

$$C_{clamp} = \left(\frac{1 \cdot 10^{-6} \text{s}}{2\pi} \right)^2 \cdot \frac{1}{5.85 \cdot 10^{-6} \mu\text{H}} = 4.32 \text{nF}$$

the AC component ΔV_{CC} ,

$$\Delta V_{CC} = \frac{\pi}{4} \cdot 1.72 \text{A} \cdot \sqrt{\frac{5.85 \mu\text{H}}{4.32 \text{nF}}} = 49.7 \text{V}$$

Minimum voltage rating of the capacitor,

$$V_{MIN_CC} = 20 \text{V} \cdot \frac{49 \text{T}}{7 \text{T}} + 49.7 \text{V} = 190 \text{V} (250 \text{V})$$

Clamp resistor

The optimal point to turn-on the AC FET is when active clamp current is flowing through the AC FET body diode (ZVS) and optimal point to turn-off is when active clamp current is close to zero (ZCS) or the AC FET body diode is conducting (ZVS). If the variation of the leakage inductance and clamp capacitor value (ex. C0G) can be controlled within 0.7-1.4x of nominal value a series clamp resistor is not required (ZVS will be achieved during turn on and turn off).

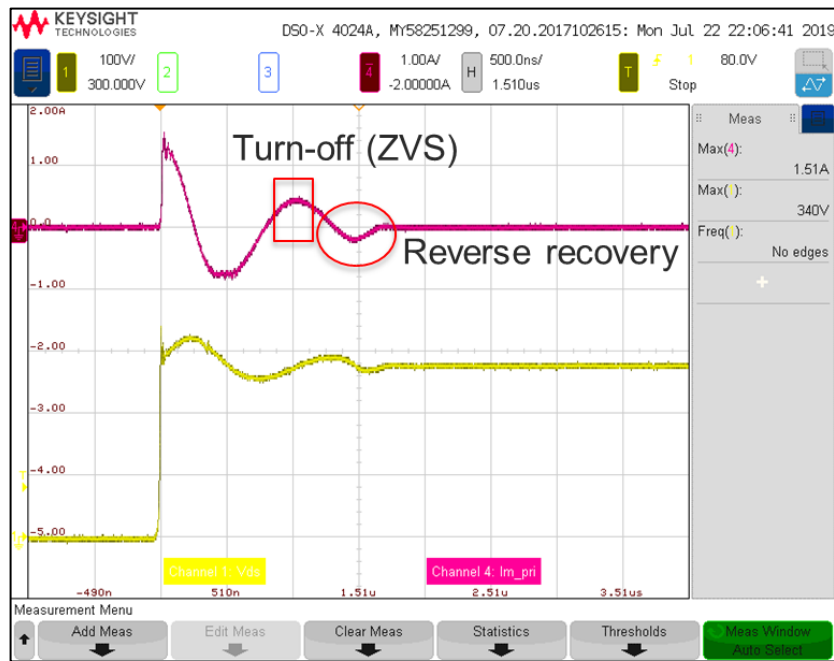


Figure 11: 115Vac/20V/3A w/o clamp resistor. CH1 is the primary MOSFET drain voltage and CH4 is the active clamp current (positive from source-to-drain).

If the leakage inductance cannot be well controlled (within 0.7-1.4x), it is recommended to add a clamp resistor in series, typically 10R-20R (10R 1812 footprint, 20R 2512), to ensure the AC FET turn-off is soft-switched (ZCS). Figure 11 illustrates the active clamp current without a clamp resistor (ZVS turn-on and turn-off) and Figure 12 illustrates the active clamp current with a 20R clamp resistor (ZVS turn-on and ZCS turn-off).

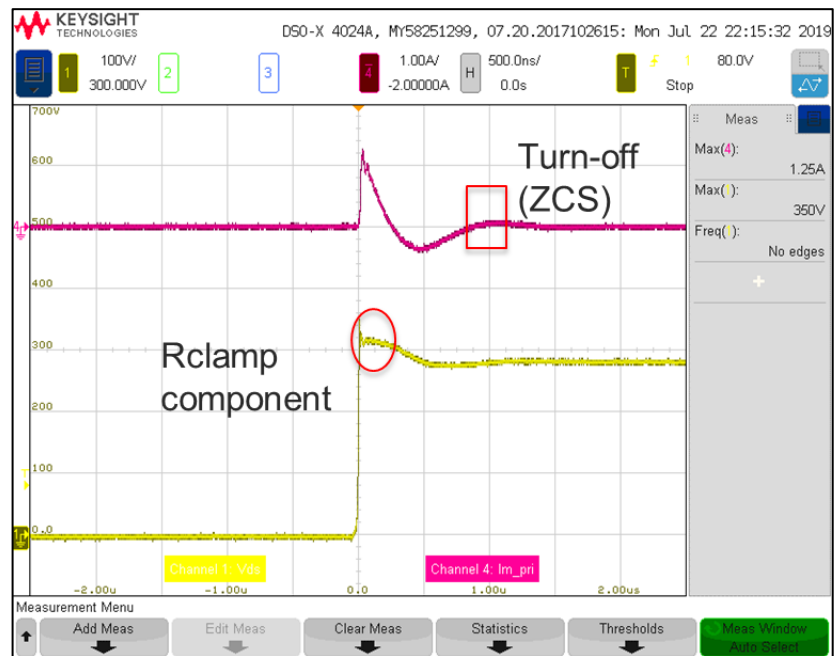


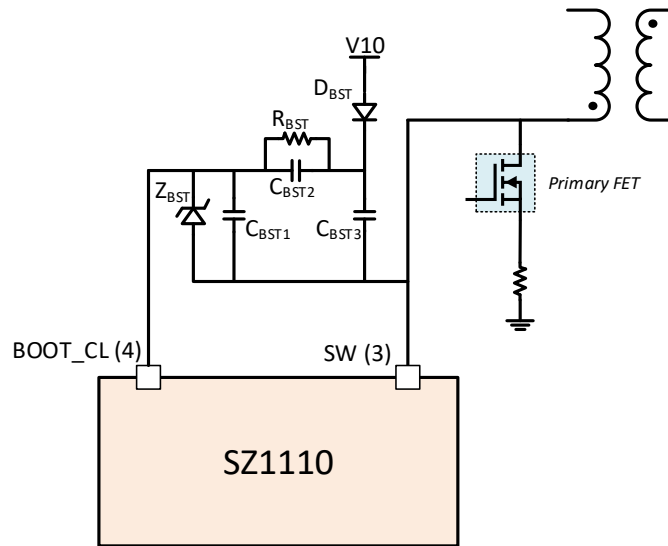
Figure 12: 115Vac/20V/3A w/ 20R clamp resistor. CH1 is the primary MOSFET drain voltage and CH4 is the active-clamp current (positive from source-to-drain).

Active clamp FET parallel diode

An external parallel diode is required in the circuit to prevent the AC FET damage during single point failure periods when start-up regulator can be on, drawing current through the body diode, and the primary MOSFET turn-on events with large negative primary drain dv/dt slew-rate, -20V/ns.

Parameter	Value
Max DC reverse voltage	$\geq 800\text{V}$
Average rectified current	$\geq 1\text{ A}$
Reverse recovery time (trr)	$\leq 75\text{ns}$
VF @ 10mA	$\leq 0.6\text{V}$
Recommended parts	US1MFA, HS1KFL

Table 3: Clamp diode selection criteria

Step 11: Determine the active clamp gate-driver supply bootstrap components**Figure 13: Bootstrap capacitor circuit**

The voltage supply to the internal AC FET high side driver is provided by the C_{BST1} connected between the BOOT_CL & SW pin. To ensure that ACFET is active after the startup, the C_{BST1} must be sufficiently charged above ACFET driver UVLO ($\sim 3.6\text{V}$ typical). An enhanced BOOT_CL charging circuit is implemented which comprises of C_{BST3} , a capacitor divider (C_{BST2} , C_{BST1}) and a Zener diode, to regulate the voltage between BOOT_CL and SW.

The enhanced charging circuit has two objectives: First, the peak overshoot due to the inrush current during the first pulse should be below Max BOOT_CL voltage rating (5.5V) and second, is to charge the C_{BST1} to above 0.5V during the first pulse. The selection of the capacitor divider value is based on the experimental observation. For example, if the C_{BST3} between SW and D_{BST} is charged to $\sim 6\text{V}$ during the 1st pulse in room temp with 10Ω R_{gate} , then the capacitor divider of 10nF (C_{BST1}) and 47nF (C_{BST2}) would charge BOOT_CL to $\sim 2.7\text{V}$ as shown in Figure 14. Over the time, when C_{BST3} is charged to a higher value, the Zener diode would clamp the voltage across the C_{BST1} to a safe range for ACFET gate driver.

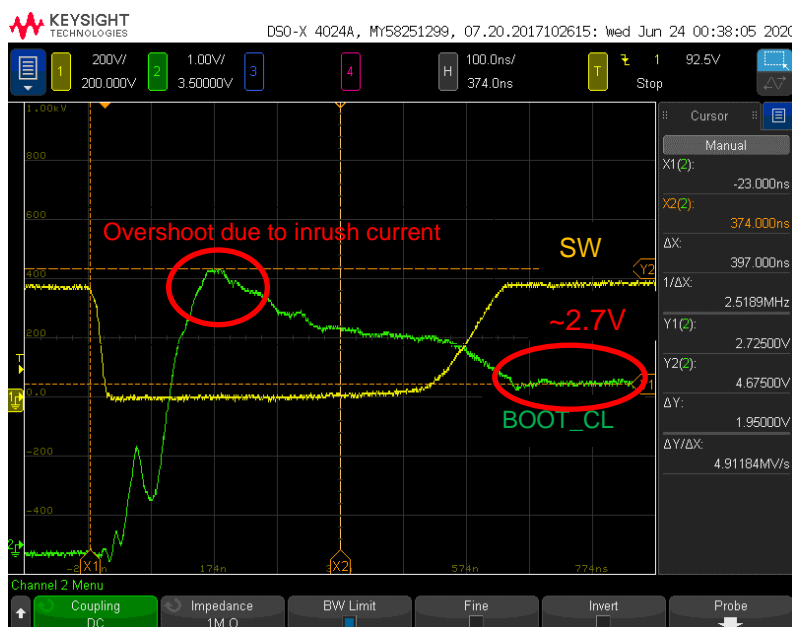


Figure 14: BOOT_CL voltage charged to ~2.7 during the first pulse

It should also be noted that C_{BST1} needs to be sized to limit the worst-case steady state ripple to ~100 mV. To limit the voltage ripple within 100 mV, C_{BST1} needs to be at least 10 nF.

Design example

The recommended values

Parameter	Value
C_{BST1}	10nF (50V, X7R)
Z_{BST}	MM3Z4V7B
C_{BST2}	47nF
C_{BST3}	3.3nF
R_{BST}	3.3k Ω
D_{BST}	US1MFA

Step 12: V10 Capacitor Sizing

V10 is the SZ1110 supply voltage input (8.6 V to 10.5 V) that provides power to the internal circuits, including the primary FET gate driver, the 5 V LDO and the bootstrap circuit for the internal Active Clamp FET driver. The V10 should always be above the startup regulator turn-on threshold V_{ON_V10} (8.55V maximum). It is recommended to use a large cap at first, typical recommendation is 47uF e-capacitor and 1uF ceramic capacitor. The selection of the optimal V10 cap value is based on the experimental observation.

For example, the Figure 15 is the start-up at 90Vac and -40°C ambient temperature with recommended 47uF e-cap and 1uF ceramic capacitor. The V10 voltage is above 8.5V before Auxiliary winding takes over.

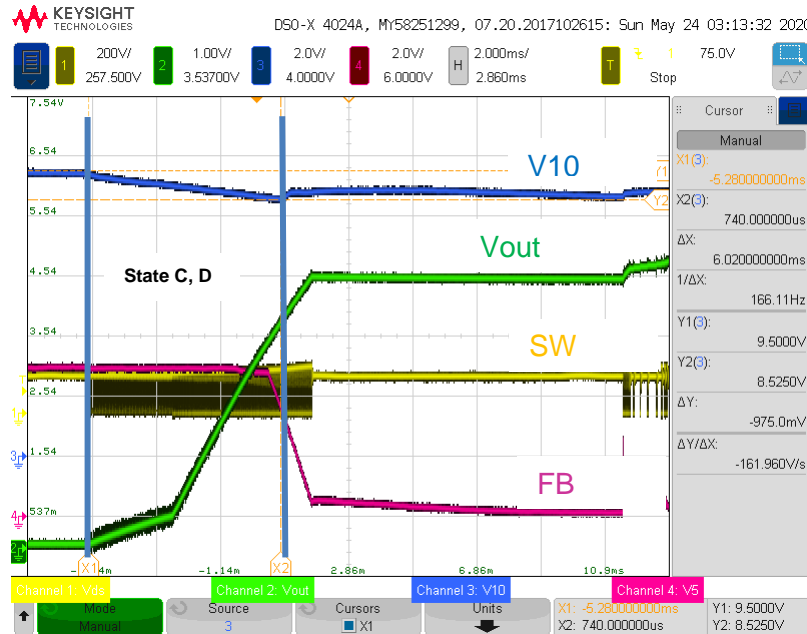


Figure 15: V10 voltage waveform during the start-up

The time needed for the auxiliary winding to take over from the start-up LDO depends how fast output voltage rises and turns ratio between auxiliary and secondary (State C, D). If the time taken by the auxiliary regulator to take over is assumed to be independent of V10 cap value, the theoretical capacitance value can then be calculated by the following equation:

$$C_1 = C_2 \cdot \frac{dv_2}{dv_1}$$

where C_1 is the design value, C_2 is the initial value, dv_2 is target voltage drop, and dv_1 is the voltage drop with initial V10 value. In case, a user chooses to set the minimum V10 voltage to a different value, ex. 9V, then the new V10 capacitance value can be calculated as.

$$C_1 = 57\mu F \cdot \frac{9.5-8.5}{9.5-9} = 114\mu F$$

Note: To account for IC variations like IC current consumption, V10 capacitance, and QR detection sensitivity, it is recommended to provide some margin on minimum V10 voltage. Hence, it is advised to set the voltage >8.6V.

Step 13: Auxiliary regulator circuit

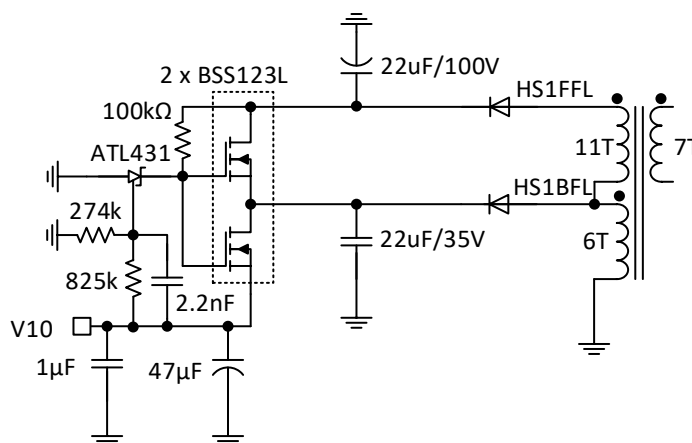


Figure 16: Dual-winding auxiliary regulator circuit for high performance USB PD applications and wide range of ambient temperature (-40 to 150°C) operation

During startup, an integrated UHV start-up regulator provides power to Pin 7 (V10), until the more power efficient auxiliary winding takes over. For applications where the output voltage may vary over a wide range, such as USB-PD or Quick Charge, the reflected rectified auxiliary winding voltage will be outside of the acceptable V10 pin voltage range. As a result, a discrete external regulator will be required to provide regulated power to V10 from the rectified auxiliary winding node. In such applications, where the output voltage may vary from 5 to 20 V a dual-auxiliary winding and dual MOSFET external regulator, as shown in Figure 16, is recommended to minimize SZ1110 power losses during maximum output voltage operation. The auxiliary regulator of Figure 16 will also ensure that the V10 voltage is tightly regulated regardless of component tolerances and temperature variations (-40 to 150°C).

It should be noted that a low minimum cathode current shunt regulator, <150uA, (such as ATL431, LR431ATLT1G, or TL432-1%) are desirable as they allow for reduction of quiescent current draw and subsequent no-load power. The shunt regulator quiescent current resistor should be sized according to the maximum required cathode current and is given by equation

$$R_{KA} < \frac{3.5}{I_{KA}^{min}}$$

The external regulator component voltage ratings should be based on the maximum positive and negative reflected voltage on the auxiliary winding as given below equation. This requirement must be considered for both steady state and transient, including fault conditions.

$$V_{AUX}^{MAX} = \left(V_{OUT_MAX} \cdot \frac{N_{AUX}}{N_{SEC}} \right)$$

$$V_{AUX}^{MIN} = - \left(V_{BULK_MAX} \cdot \frac{N_{AUX}}{N_{PRI}} \right)$$

Note:

The LDO MOSFET's should be selected based on the maximum V_{AUX1} , V_{AUX2} voltages measured on the bench. The minimum V_{DS} rating of the dual LDO MOSFET's used in a 20V, 30W application is 60V. Theoretically, the max voltage on the V_{AUX1} should be ~53V from the above equation. However, due to the leakage inductance, the auxiliary capacitors see higher voltage than the theoretical value. The maximum voltage on the auxiliary is observed to be ~85V; therefore, the maximum voltage across drain-source of the dual MOSFET is ~60V.

Over-voltage Fault:

In case of output over voltage fault, the voltage difference between V_{AUX1} and V_{AUX2} can be considerably higher compared to the steady state before the fault is detected. Hence, the values of V_{AUX1} and V_{AUX2} capacitors and the voltage rating of MOSFET pair must be considered taking this into account.

For an example, during the USB-PD FB to SGND short, if V_{AUX2} discharges faster than V_{AUX1} then the dual MOSFET could potentially see more than the rated VDS voltage. Hence, the bottom bias winding capacitance value (in Step 7) is calculated such that it's discharge rate is slower than the bus capacitance discharge rate in case of output over voltage fault. Figure 17 is the waveform captured during the output OVLO fault with the calculated V_{AUX2} capacitance value (33uF). The maximum value of the V_{AUX1} - V_{AUX2} voltage observed is ~55V, which is within the safe operating area of the LDO MOSFET.

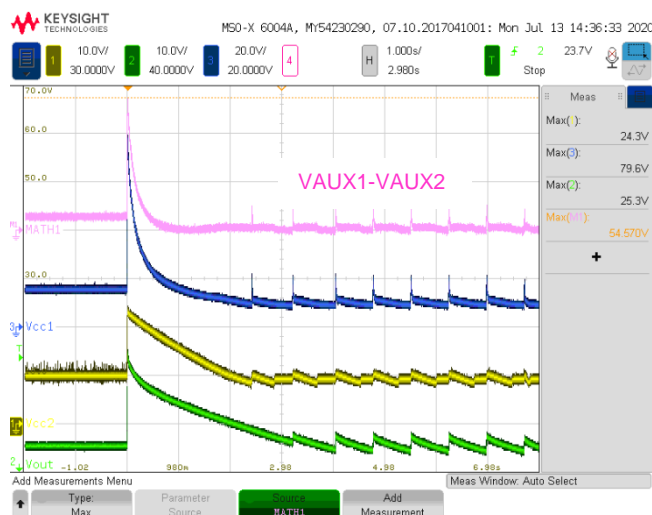


Figure 17: V_{AUX1} , V_{AUX2} waveforms captured during the over voltage fault.

Step 14: BULK_S sensing resistors

The under-voltage/brown-out/brown-in are implemented using bulk capacitor voltage sensing with a resistor divider connected to V_{BULK_S} .

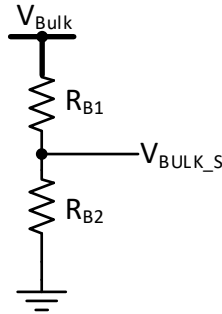
Universal line voltage range (82 Vac to 300 Vac)

Figure 18: Simple bulk voltage sensing circuit

A basic resistor divider, as shown in Figure 18, can be utilized to ensure operation over universal line voltage range with margin. To minimize the no-load power a large R_{B1} resistance value, $4 \times 22M\Omega$, is recommended.

The BULK_S pull-down resistance should be calculated taking into account the desired maximum brown-in voltage ($V_{AC}^{brown-in}$), the BULK_S brown-in threshold V_{UV_REC} (0.655V), and the desired R_{B1} resistance value. Both R_{B1} & R_{B2} are recommended to be within 1% tolerance.

$$R_{B2} = \frac{R_{B1}}{\left(\frac{V_{BULK}^{brown-in}}{V_{UV_REC}} - 1\right)} = \frac{88M\Omega}{\frac{V_{AC}^{brown-in} \cdot \sqrt{2}}{0.575V} - 1}$$

Once R_{B1} and R_{B2} are calculated the minimum AC line OVLO voltage can be determined using the minimum BULK_S OVLO threshold V_{OVLO_TH} (2.09V) and the following equation:

$$V_{AC}^{OVLO} = \frac{1}{\sqrt{2}} \cdot V_{OVLO_TH} \cdot \left(\frac{R_{B1}}{R_{B2}} + 1\right) = \frac{2.09V}{\sqrt{2}} \cdot \left(\frac{88M\Omega}{R_{B2}} + 1\right)$$

Furthermore, the minimum AC line OVLO recovery voltage can be determined using the minimum BULK_S recovery from over-voltage threshold V_{OVLO_REC} (2.05V) and the following equation:

$$V_{AC}^{OVLO_Rec} = \frac{1}{\sqrt{2}} \cdot V_{OVLO_REC} \cdot \left(\frac{R_{B1}}{R_{B2}} + 1\right) = \frac{2.05V}{\sqrt{2}} \cdot \left(\frac{88M\Omega}{R_{B2}} + 1\right)$$

Design Example – Universal Line Voltage

The desired maximum brown-in voltage is set to 82Vac to ensure sufficient margin for input AC line variations and BULK_S resistor divider ratio accuracy. For this application we wish to minimize no-load power; therefore, the BULK_S pull-up resistance is chosen to be 4x22M (88MΩ). Finally, the required pull-down resistance is calculated to be equal to

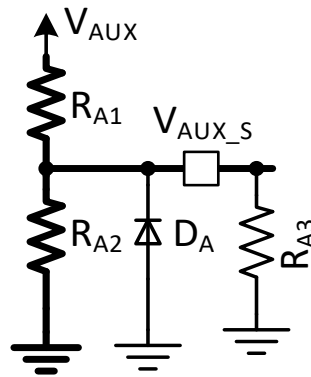
$$R_{B2} = \frac{88M\Omega}{\frac{82Vac \cdot \sqrt{2}}{0.575V} - 1} = 438.5k\Omega = 438K\Omega \text{ (standard value)}$$

Utilizing R_{B1} and R_{B2} the minimum AC OVLO and AC OVLO recovery voltages are calculated

$$\text{Minimum AC OVLO : } V_{AC}^{OVLO} = \frac{2.09V}{\sqrt{2}} \cdot \left(\frac{88M\Omega}{438k\Omega} + 1 \right) = 298Vac$$

$$\text{Minimum AC OVLO recovery : } V_{AC}^{OVLO_Rec} = \frac{2.05V}{\sqrt{2}} \cdot \left(\frac{88M\Omega}{438k\Omega} + 1 \right) = 293Vac$$

Step 15: VAUX_S winding voltage resistors

Figure 19: V_{AUX} voltage sense circuit

V_{AUX_S} is the sensing pin for attenuated auxiliary voltage and is primarily utilized to support Quasi-Resonant (QR) mode of operation. An internal QR valley comparator, connected to V_{AUX_S}, detects the QR valley points. Furthermore, QR valley comparator is used to change the mode of operation from fixed frequency DCM to valley switching DCM during start-up and to provide output short circuit protection.

For sensing the reflected voltage on the auxiliary winding, a resistor divider is placed at the V_{AUX_S} pin (R_{A1} and R_{A2}) in addition to a silicon clamping diode (to clamp negative V_{AUX} voltage).

$$V_{VAUX_S} = \frac{R_{A2} || R_{A3}}{R_{A1} + R_{A2} || R_{A3}} \cdot V_{AUX}$$

The optimal divider ratio depends on the maximum output voltage levels of the AC/DC converter, as well as the transformer turns ratios. R_{A1} and R_{A2} resistors values should be chosen such that, under no operating conditions, V_{AUX_S} pin voltage exceeds the absolute maximum voltage rating (±8V).

$$V_{VAUX_S}^{MAX} = \left(V_{OUT_MAX} \cdot \frac{N_{AUX}}{N_{SEC}} \right) \cdot \frac{R_{A2} || R_{A3}}{R_{A1} + R_{A2} || R_{A3}}$$

The lower resistor R_{A2} value should be selected considering potential pin-to-pin short condition between V_{AUX_S} and V_{BULK_S}. For such a fault case, it is desirable that V_{BULK_S} be pulled down below the SZ1110 BULK UVLO, V_{UV_TH} (258mV), for all expected input voltage operating conditions, such that SZ1110 remains in a non-switching state. Typical R_{A2} value required to ensure safe operation is 1/20th the value of BULK_S pull-down resistor R_{B2}. When calculating R_{A1} it is recommended to add ~10% safety margin to V_{BULK_MAX} and V_{OUT_MAX}.

It should be noted that valley detection delays can be compensated for with the use of an external capacitor, which is placed either in parallel with R_{A2} when the valley point is early, as shown in Figure 20, or which is placed in parallel with R_{A1} when the valley point is late, as shown in Figure 21.

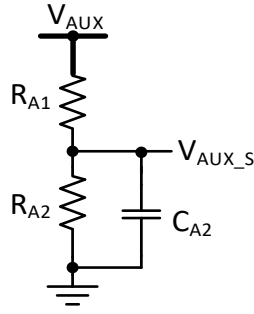


Figure 20: VAUX_S sensing circuit to add time delay.

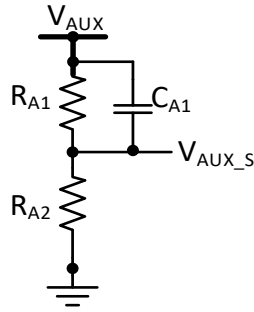


Figure 21: VAUX_S sensing circuit to add time lead.

The C_{A2} capacitor value can be calculated to meet the desired delay Δt_{delay}

$$C_{A2} = \frac{\Delta t_{delay}}{(R_{A1} || R_{A2})} - C_{DA},$$

where C_{DA} is the diode junction capacitance.

The relation between feedforward capacitance C_{A1} and time lead is given below:

$$\Delta t_{lead} = \frac{T_{QR}}{360} \cdot \left[\tan^{-1}\left(\frac{2\pi \cdot R_{A1} \cdot C_{A1}}{T_{QR}}\right) - \tan^{-1}\left(\frac{2\pi \cdot R_{A1} \cdot C_{A1}}{T_{QR}} \cdot \frac{R_{A2}}{R_{A1} + R_{A2}}\right) \right]$$

where, T_{QR} = time period of QR resonance.

Design Example

R_{A2} value should be less than $470\text{k}\Omega / 20 = 23.5\text{k}\Omega$, and the closest E24 value is 22k. The internal pull-down resistance is $60\text{k}\Omega \pm 20\%$.

The R_{A1} value can be calculated as

$$V_{AUX_S}^{MAX} = \left(V_{OUT_MAX} \cdot \frac{N_{AUX}}{N_{SEC}} \right) \cdot \frac{R_{A2} || R_{A3}}{R_{A1} + R_{A2} || R_{A3}}$$

$$8 = \left(20\text{V} \cdot 1.2 \cdot \frac{17T}{7T} \right) \cdot \frac{22\text{k}\Omega || 60\text{k}\Omega}{R_{A1} + 22\text{k}\Omega || 60\text{k}\Omega}$$

$R_{A1} = 101\text{k} \rightarrow 100\text{k}$ (E24 value)

For a delay $\Delta t = 100\text{ns}$, the capacitor is calculated as

$$C_{A2} = \frac{100\text{ns}}{(100\text{k} || 16.1\text{k})} = 7.2\text{pF} = 6.8\text{pF} \text{ (Standard value)}$$

Step 16: OTP sensing

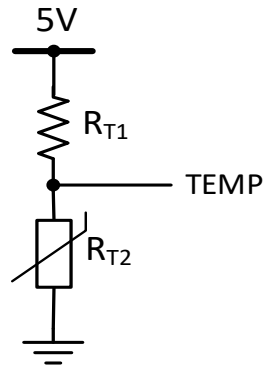


Figure 22: Over temperature sensing circuit

A second temperature monitor is provided by an external NTC (negative temperature coefficient) thermistor. The R_{T2} connected from TEMP pin to ground can be used to give over-temperature protection to the power supply from hotspots on the printed circuit board. At start-up, the voltage at TEMP needs to be higher than $V_{NTCR}=1V$ for the IC to start operation. If the voltage at TEMP is lower than $V_{NTCTH} = 0.61V$ after the start-up, the IC shuts down and recovery from shutdown takes place once the voltage is above $1V$.

Once OTP set point and R_{T2} are determined the pull-up resistor R_{T1} can be determined using the minimum TEMP_S threshold V_{NTC_TH} ($0.61V$) and the following equation:

Design Example

NCP15WL104E03RC (100k resistor at $25^{\circ}C$) is selected as the NTC resistor for the reference design. For a desired external OTP set point of $95^{\circ}C$ R_{T1} pull up resistor is calculated as:

$$V_{NTC_TH} = 5V \cdot \frac{R_{T2}^{120^{\circ}C}}{R_{T1} + R_{T2}^{120^{\circ}C}}$$

$$V_{NTC_TH} = 5V \cdot \frac{R_{T2}^{95^{\circ}C}}{R_{T1} + R_{T2}^{95^{\circ}C}}$$

$$0.61V = 5V \cdot \frac{5.7k}{R_{T1} + 5.7k}$$

$$R_{T1} = 41k$$

Step 17: OOV_P_S sensing resistors

The OOV_P_S pin senses the reflected output voltage through the auxiliary winding using a resistor divider circuit connected after the auxiliary rectifying diode as shown in Figure 23. During start-up, output over-voltage protection is triggered when the voltage at pin OOV_P_S exceeds V_{OOVP_TH} (1.4V). Recovery from output over-voltage condition requires OOV_P_S pin voltage to drop below V_{OOVP_REC} (1.08V). During steady state, output over-voltage protection is provided by sensing the V_{FB} pin voltage, specifically when FB is pulled up to V_{5OUT} for extended period.

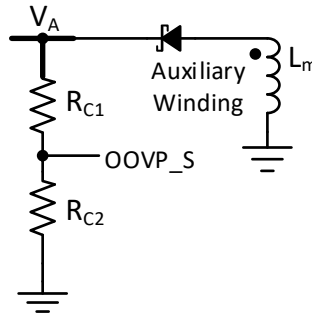


Figure 23: Resistor Divider for Output OVP Sensing

The following equation calculates the voltage at OOV_P_S pin.

$$V_{OOVP_S} = \frac{R_{C2}}{R_{C1} + R_{C2}} \cdot V_A$$

Where, V_A is the rectified auxiliary voltage, as shown in Figure 23.

The lower resistor R_{C2} value, like R_{A2} , should be selected considering potential pin-to-pin short condition between V_{OOVP_S} and V_{BULK_S} . For such a fault case, it is desirable that V_{BULK_S} be pulled down below the SZ1110 BULK UVLO, V_{UV_TH} (258mV), for all expected input voltage operating conditions, such that SZ1110 remains in a non-switching state.

Note: It is also recommended to use a Zener diode (connected between the Anode of the optocoupler and SGND) to provide Output over voltage protection in case of USB -PD IC VFB to SGND single-point failure.

Maximum Output Voltage	OOVP Zener	OOVP Voltage
5	MMSZ5235B	9
9	MMSZ5241B	14
12	MMSZ5245B	18
15	MMSZ5248B	21
20	MMSZ5251B	25
21	MMSZ5251B	25
24	MMSZ5252B	27

Table 4: Recommended Output Over Voltage protection Zener with respect to the Maximum output voltage.

Design Example

R_{C2} is selected to be equal to R_{A2} , 22k. With the output OOVp threshold set to 8V, the corresponding reflected voltage on auxiliary winding, V_A is calculated as:

$$V_A = V_{OUT} \cdot \frac{N_{AUX}}{N_{SEC}} = 8V \cdot \frac{17T}{7T} = 19.4V$$

R_{C1} can now be calculated using the equation,

$$V_{OOVP_S} = \frac{R_{C2}}{R_{C1} + R_{C2}} \cdot V_A$$

$$1.4 = \frac{22k}{R_{C1} + 22k} \cdot 19.4V$$

$$R_{C1} = 280k\Omega$$

Note: Fine tuning of RA1 may be required depending on the auxiliary winding parasitic inductance (coupling factor between secondary and auxiliary windings).

Step 18: Conducted EMI Filter design and radiated EMI considerations

The Conducted EMI noises are generated from power supplies due to the switching actions of the semiconductor devices. Although the EMI regulation specifications (CISPR22-Class B) target the total EMI emission for SMPS, the noises can be categorized into differential-mode and common-mode noises to minimize each noise more effectively for an overall emission suppression.

In low frequency band ($< 400\text{kHz}$), differential mode noise is usually the main noise source, and the common mode noise is dominant at high frequency range. Due to circuit parasitic and fast switching nature of power devices, extra effort is required to determine the noise attenuation requirement at the ultra HF band, typically in the frequency range of 5M to 20MHz. Since the circuit parasitic is difficult to quantize, the EMI design is usually an iterative effort following steps as described below.

1. Determine the attenuation requirement on the differential mode noise.
The nominal switching frequency of the converter is $\sim 100\text{kHz}$ and since the CISPR-22 starts with 150kHz . The harmonics of interest would be the 1st to 3rd harmonics of switching frequency noise in the range of 200kHz to 300kHz .
2. Determine the attenuation requirement on the common mode noise.
The uasi-resonance frequency generates main CM noise in the 600kHz range. The good approach is to determine the CM inductance requirement at this frequency band.
3. To attenuate the ultra HF noise ($> 10\text{MHz}$), usually from the circuit parasitic and switching power devices, an additional small CMC, with minimum parasitic capacitance may be required.
 - a. Alternatively, a solid ground plane underneath SZ1110 and surrounding external components and/or grounded heatsink wrapped around the primary side FET and transformer can be added. It should be noted that both methods are excellent at reducing radiated EMI noise as well.
 - b. A ferrite bead, placed on the drain or source of the primary FET, can also be an effective mitigation method for radiated EMI noise that can be generated during primary FET turn-off. The peak attenuation frequency should be chosen to match the frequency of the noise that is generated during turn-off (typically in the $80\text{-}120\text{MHz}$ range).

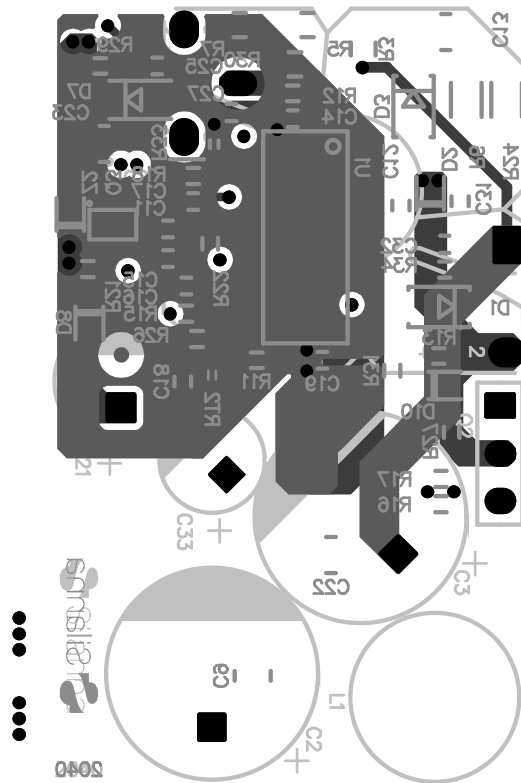


Figure 24: Recommended solid ground plane location under SZ1110 and surrounding primary side components for improved conducted and radiated EMI performance. The ground plane should be kept away from input filter (bulk capacitors, chokes, etc).

In addition to the common mode & differential mode chokes, X-capacitor (connected between Line and Neutral) and Y-capacitor (connected between primary and secondary ground) are used to filter out the noises. The Y-capacitor provides a low impedance return path for currents generated by the switching voltages between the primary and secondary windings of the transformer. A well-designed transformer with noise cancelling technique would require a smaller Y-capacitor. *Please discuss with your FAE how Silanna's propriety noise cancelling winding technique can be utilized in this regard.*

Recommended values

Differential inductor = 60-100uH (placed between bulk capacitors in Pi configuration)

X-cap = 100nF

Y-cap = 680-2200 pF

4-Layer PCB design with solid ground plane. Ground plane should not be poured near the input filter components or traces (bulk capacitor, differential inductor, X-Cap, etc)

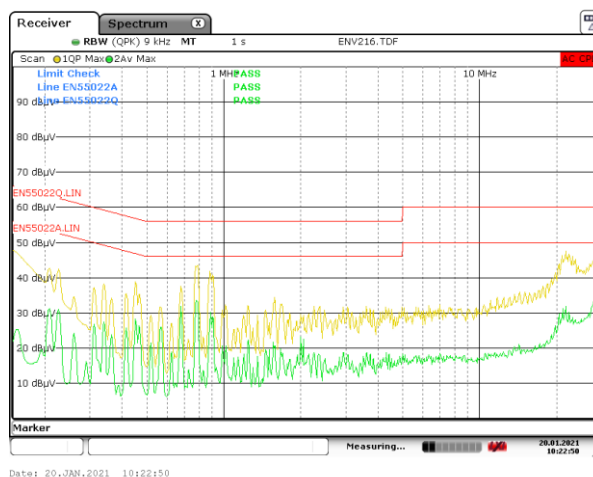


Figure 25: Worst case conducted EMI spectrum captured on our EVB with floating output at high line (230Vac) and 20V/1.5A with single 100uH differential inductor, 100nF X-capacitor and 1000pF Y-capacitor.

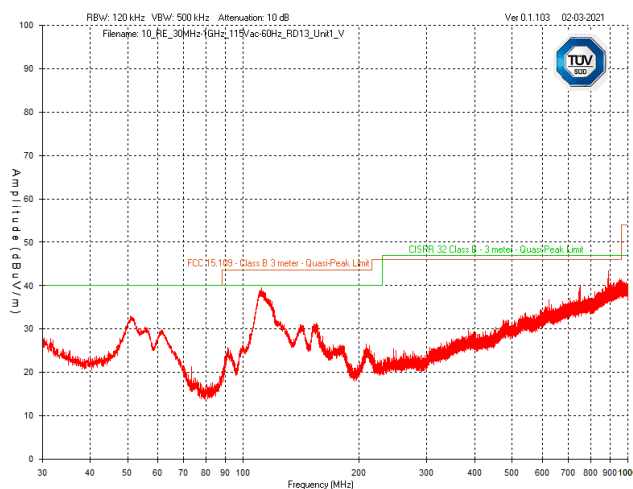
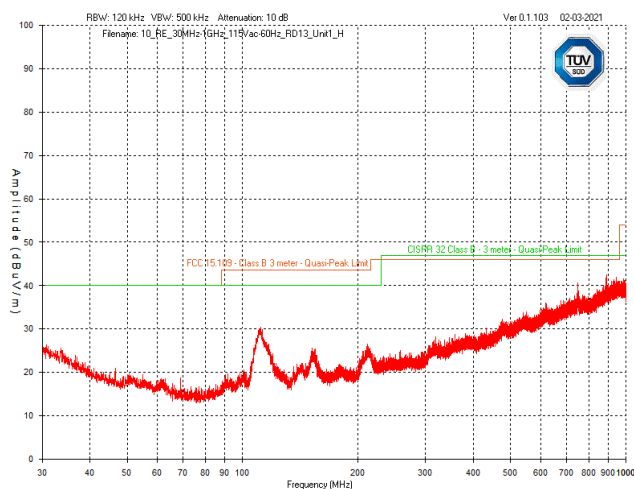


Figure 26: 15 V/2 A Radiated EMI measurement results for 115 Vac in Horizontal and Vertical orientation for unit 1.

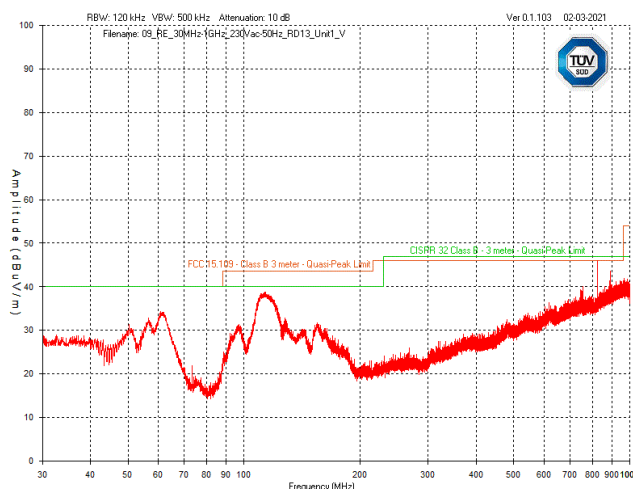
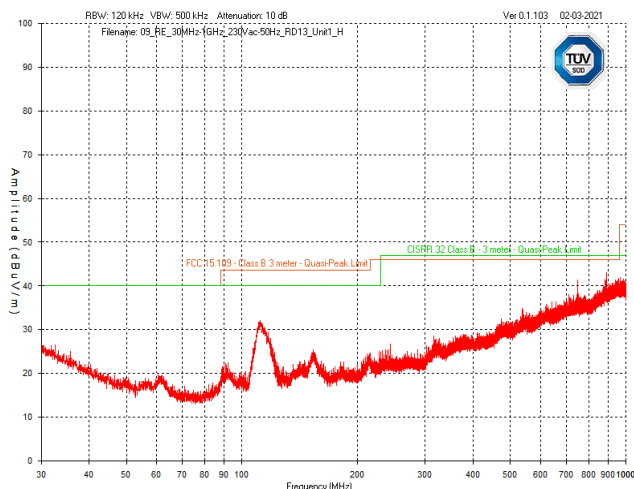


Figure 27: 15 V/2 A Radiated EMI measurement results for 230 Vac in Horizontal and Vertical orientation for unit 1.

Revision History

Date	Revision	Notes	Author
2/26/2021	1.0	Initial Release	AR